

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

S8050-MS

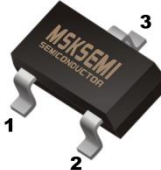

Product specification

TRANSISTOR (NPN)

FEATURES

Complimentary to S8550-MS

 Collector Current: $I_C=0.5A$
Reference News

PACKAGE OUTLINE	MARKING
 <p>1. BASE 2. EMITTER 3. COLLECTOR</p>	
SOT-23	

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	40	V
V_{CE0}	Collector-Emitter Voltage	25	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Dissipation	0.3	W
R_{JA}	Thermal Resistance from Junction to Ambient	417	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

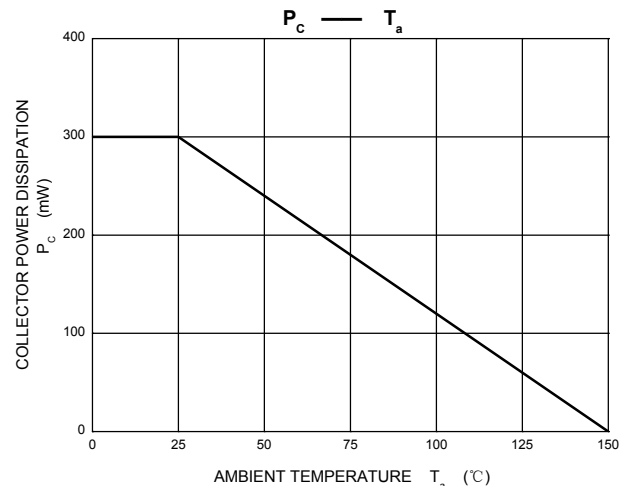
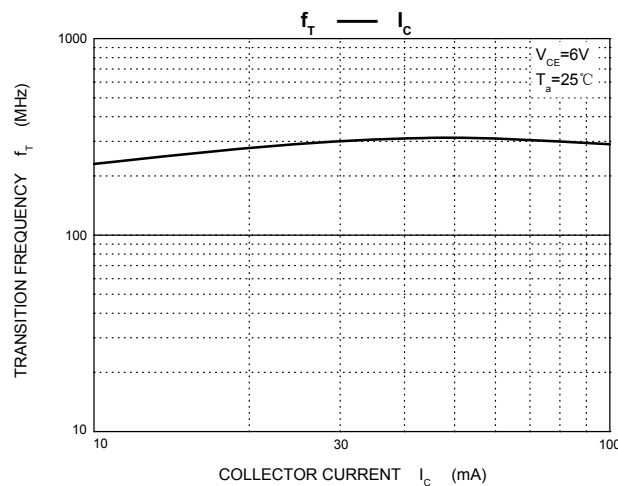
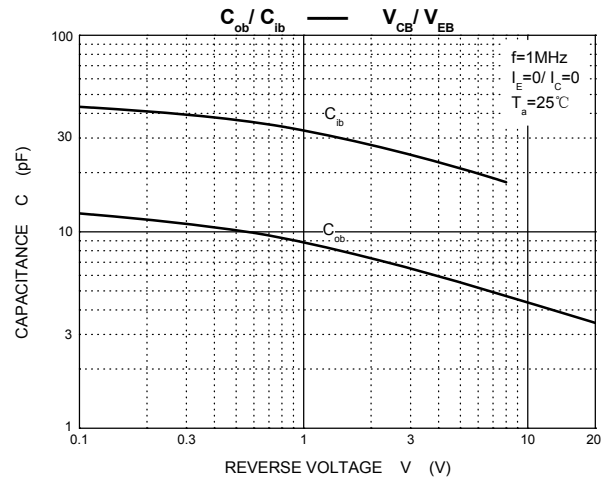
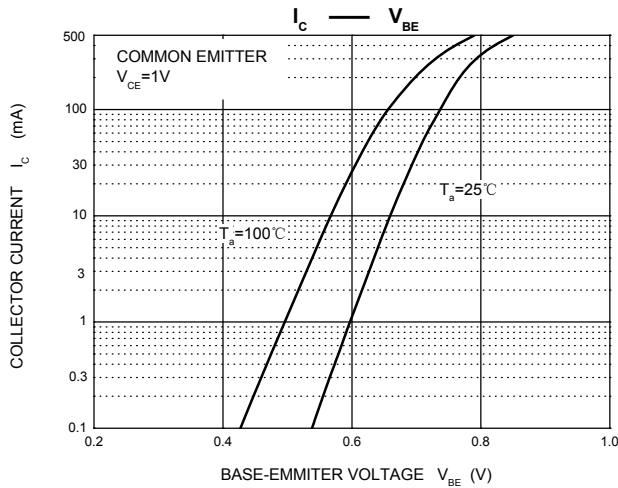
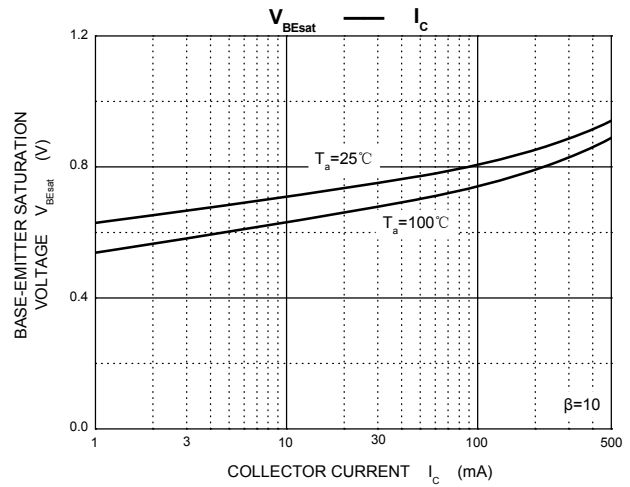
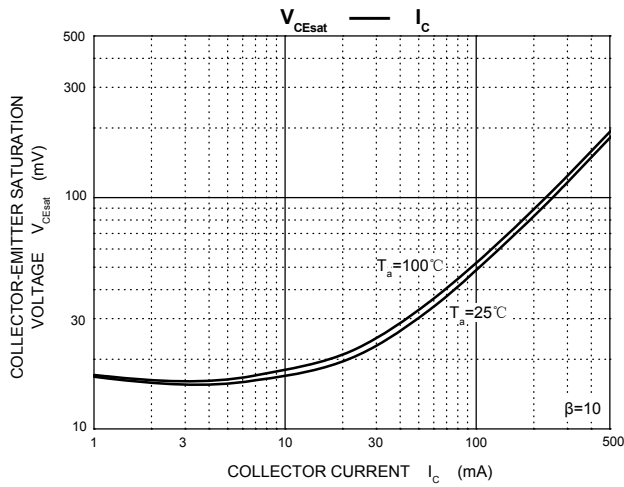
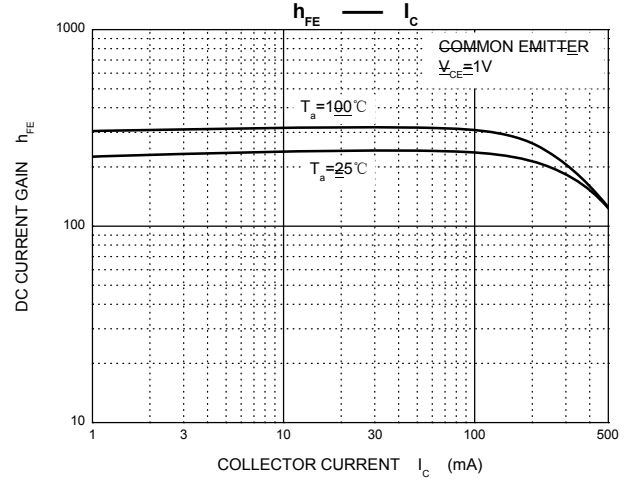
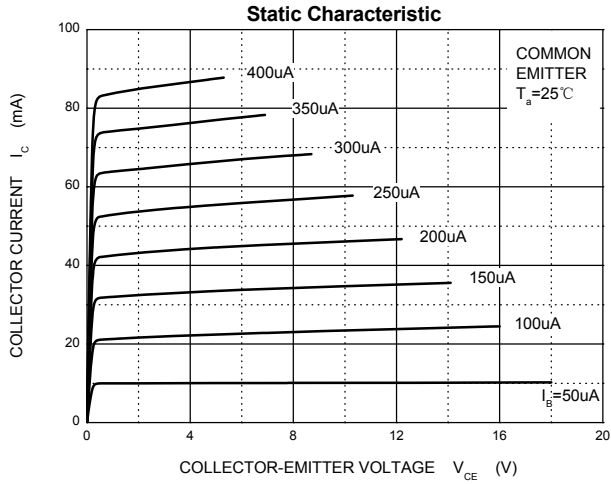
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=50mA$	120		400	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I=500mA, I_B=50mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$			1.2	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA$ $f=30MHz$	150			MHz

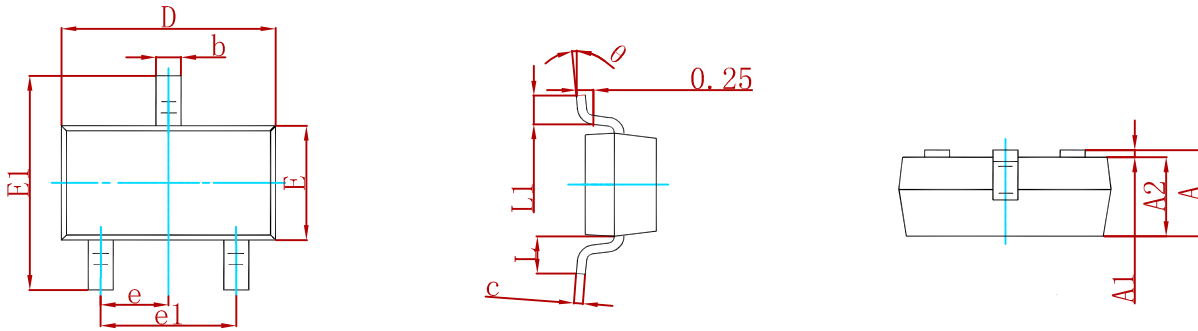
CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

Typical Characteristics

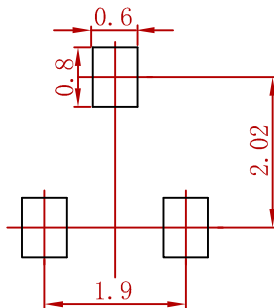


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
S8050-MS	SOT-23	3000

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